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### (54) COMPOSITION FOR FORMING ANTIREFLECTION FILM AND RESIST PATTERN FORMING METHOD

(57)Abstract:

PROBLEM TO BE SOLVED: To provide a composition for forming an antireflection film having a higher dry etching rate than a photoresist.

SOLUTION: The composition contains (A) at least one compound selected from a compound of the formula  $\text{Si}(\text{OR}1)_a(\text{OR}2)_b(\text{OR}3)_c(\text{OR}4)_d$  (where R1-R4 are each a 1-4C alkyl or phenyl), a compound of the formula  $\text{R}5\text{Si}(\text{OR}6)_e(\text{OR}7)_f(\text{OR}8)_g$  (where R5 is H, a 1-4C alkyl or phenyl and R6-R8 are each a 1-3C alkyl or phenyl) and a compound of the formula  $\text{R}9\text{R}10\text{Si}(\text{OR}11)_h(\text{OR}12)_i$  (where R9 and R10 are each H, a 1-4C alkyl or phenyl and R11 and R12 are each a 1-3C alkyl or phenyl), and (B) at least one highly light absorbing material having a substituent capable of condensing with the component A in its structure.

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### LEGAL STATUS

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